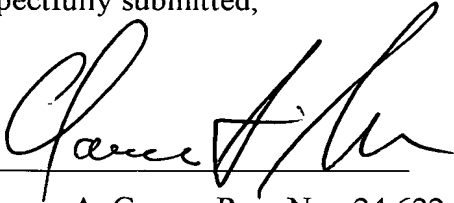


## REMARKS

In accordance with 37 C.F.R. §1.121 (as amended on 11/7/2000) the rewritten claim(s) above are shown on separate page(s) marked up to show all the changes relative to the previous version of that section.

Respectfully submitted,



Clarence A. Green, Reg. No.: 24,622

Perman & Green, LLP

435 Post Road

Fairfield, CT 06430

(203) 259-1800

Customer No.: 2512

8 March 01

Date

Application entitled: QUANTUM WELL INTERMIXING

## MARKED UP CLAIM(S)

### CLAIMS

5. A method according to ~~any preceding claim~~claim 1, including the step of masking a portion of the structure to control the degree of radiation damage.
8. A method according to ~~any of claims 5 to 7~~claim 5, in which the mask is selected from a group consisting of binary masks, phase masks, gray masks, dielectric or metal masks, and photoresist masks.
9. A method according to ~~any preceding claim~~claim 1, in which spatial control of intermixing is controlled using a variable profile mask pattern.
10. A method according to ~~any preceding claim~~claim 1 further comprising the steps of forming a photoresist on the structure and differentially exposing regions of the photoresist in a spatially selective manner in dependence on the degree of quantum well intermixing required, and subsequently developing the photoresist.
13. A method according to ~~any of claims 10 to 12~~claim 10, in which the photoresist is applied to a masking layer.
15. A method according to ~~claims 13 or 14~~, further comprising the step of etching the structure with the developed photoresist in situ to provide a differentially etched masking layer.
16. A method according to ~~any preceding claim~~claim 1, in which an electron cyclotron resonance system is used to generate a plasma, wherein the microwave power of the ECR system is between 300 and 3000 W, more preferably between 1000 and 2000 W, the process temperature is between 25 and 500°C, more preferably between 25 and 200°C, the process pressure is between 0.1 and 100 mTorr, more

preferably between 20 and 50 mTorr, and the exposure time is between 30 seconds and 1 hour, more preferably between 4 and 14 minutes.